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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101faa100fp-30

Table 1-1. List of Ordering Part Numbers

(6/12)

Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
48 pins	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Mounted	A D G	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0, R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0, R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0, R5F100GLANA#U0 R5F100GAANA#W0, R5F100GCANA#W0, R5F100GDANA#W0, R5F100GEANA#W0, R5F100GFANA#W0, R5F100GGANA#W0, R5F100GHANA#W0, R5F100GJANA#W0, R5F100GKANA#W0, R5F100GLANA#W0 R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0, R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0, R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0, R5F100GLDNA#U0 R5F100GADNA#W0, R5F100GCDNA#W0, R5F100GDDNA#W0, R5F100GEDNA#W0, R5F100GFDNA#W0, R5F100GGDNA#W0, R5F100GHDNA#W0, R5F100GJDNA#W0, R5F100GKDNA#W0, R5F100GLDNA#W0 R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0, R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0, R5F100GHGNA#U0, R5F100GJGNA#U0 R5F100GAGNA#W0, R5F100GCGNA#W0, R5F100GDGNA#W0, R5F100GEGNA#W0, R5F100GFGNA#W0, R5F100GGGNA#W0, R5F100GHGNA#W0, R5F100GJGNA#W0
	Not mounted	A D		R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0, R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0, R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0, R5F101GLANA#U0 R5F101GAANA#W0, R5F101GCANA#W0, R5F101GDANA#W0, R5F101GEANA#W0, R5F101GFANA#W0, R5F101GGANA#W0, R5F101GHANA#W0, R5F101GJANA#W0, R5F101GKANA#W0, R5F101GLANA#W0 R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0, R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0, R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0, R5F101GLDNA#U0 R5F101GADNA#W0, R5F101GCDNA#W0, R5F101GDDNA#W0, R5F101GEDNA#W0, R5F101GFDNA#W0, R5F101GGDNA#W0, R5F101GHDNA#W0, R5F101GJDNA#W0, R5F101GKDNA#W0, R5F101GLDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(8/12)

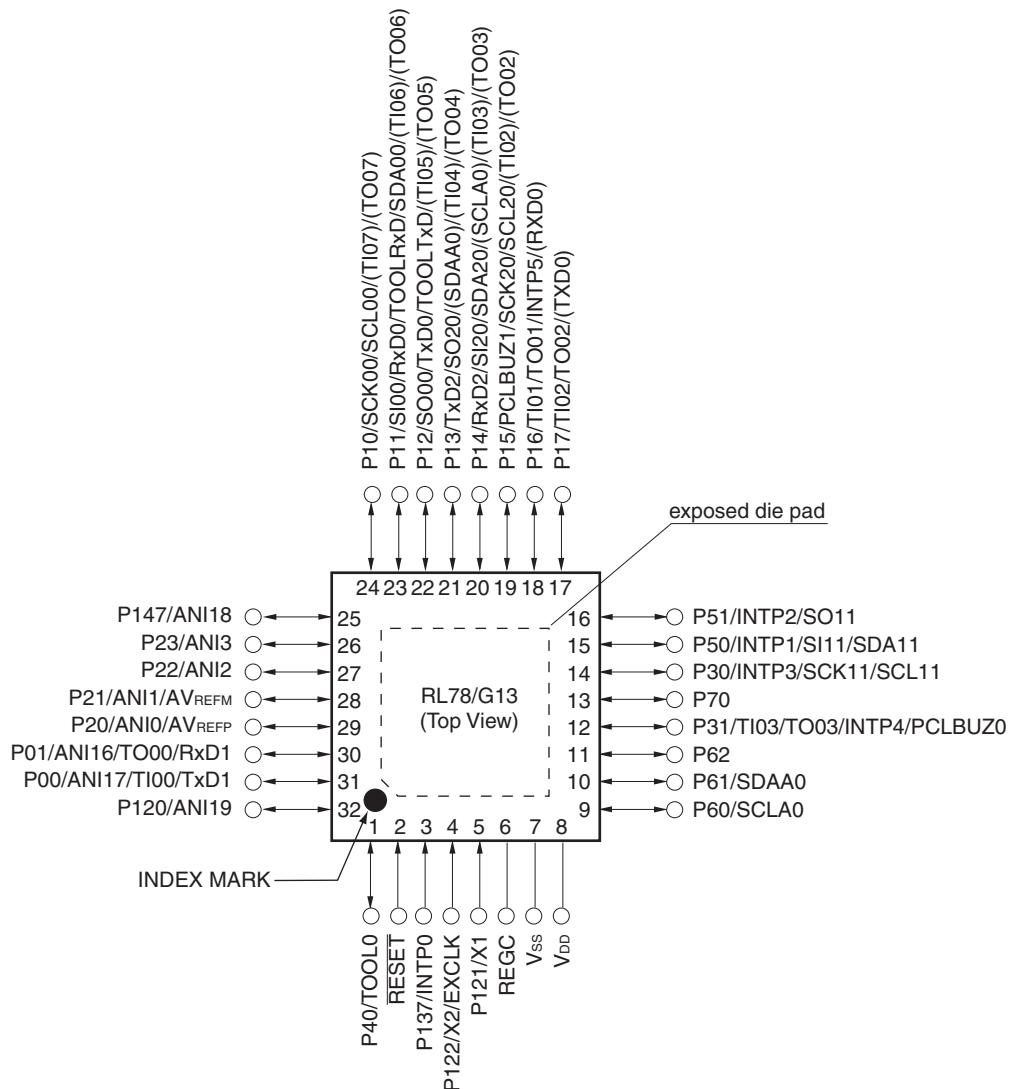
Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)	Mounted	A D G	R5F100LCAFA#V0, R5F100LDAFA#V0, R5F100LEAFA#V0, R5F100LFAFA#V0, R5F100LGAFA#V0, R5F100LHAFA#V0, R5F100LJAFA#V0, R5F100LKAFA#V0, R5F100LLAFA#V0 R5F100LCAFA#X0, R5F100LDAFA#X0, R5F100LEAFA#X0, R5F100LFAFA#X0, R5F100LGAFA#X0, R5F100LHAFA#X0, R5F100LJAFA#X0, R5F100LKAFA#X0, R5F100LLAFA#X0 R5F100LCDFA#V0, R5F100LDDFA#V0, R5F100LEDFA#V0, R5F100LF DFA#V0, R5F100LGDFA#V0, R5F100LHDFA#V0, R5F100LJDFA#V0, R5F100LK DFA#V0, R5F100LLDFA#V0 R5F100LCDFA#X0, R5F100LDDFA#X0, R5F100LEDFA#X0, R5F100LF DFA#X0, R5F100LGDFA#X0, R5F100LHDFA#X0, R5F100LJDFA#X0, R5F100LK DFA#X0, R5F100LLDFA#X0 R5F100LCGFA#V0, R5F100LDGFA#V0, R5F100LEGFA#V0, R5F100LFGFA#V0 R5F100LCGFA#X0, R5F100LDGFA#X0, R5F100LEGFA#X0, R5F100LFGFA#X0 R5F100LGGFA#V0, R5F100LHGFA#V0, R5F100LJGFA#V0 R5F100LGGFA#X0, R5F100LHGFA#X0, R5F100LJGFA#X0
		Not mounted	A D	R5F101LCAFA#V0, R5F101LDAFA#V0, R5F101LEAFA#V0, R5F101LFAFA#V0, R5F101LGAFA#V0, R5F101LHAFA#V0, R5F101LJAFA#V0, R5F101LKAFA#V0, R5F101LLAFA#V0 R5F101LCAFA#X0, R5F101LDAFA#X0, R5F101LEAFA#X0, R5F101LFAFA#X0, R5F101LGAFA#X0, R5F101LHAFA#X0, R5F101LJAFA#X0, R5F101LKAFA#X0, R5F101LLAFA#X0 R5F101LCDFA#V0, R5F101LDDFA#V0, R5F101LEDFA#V0, R5F101LF DFA#V0, R5F101LGDFA#V0, R5F101LHDFA#V0, R5F101LJDFA#V0, R5F101LK DFA#V0, R5F101LLDFA#V0 R5F101LCDFA#X0, R5F101LDDFA#X0, R5F101LEDFA#X0, R5F101LF DFA#X0, R5F101LGDFA#X0, R5F101LHDFA#X0, R5F101LJDFA#X0, R5F101LK DFA#X0, R5F101LLDFA#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.5 32-pin products

- 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)

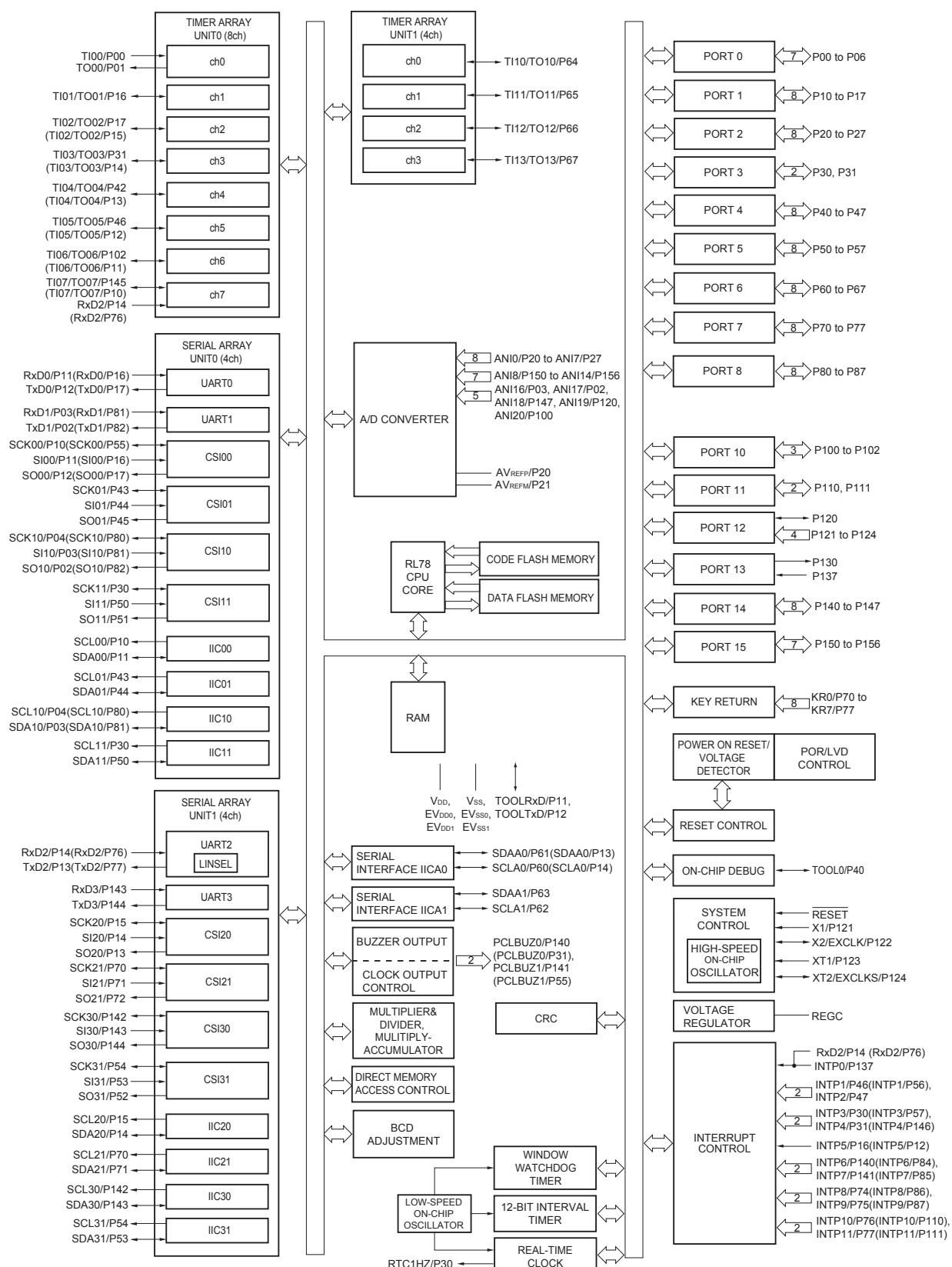


Caution Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
3. It is recommended to connect an exposed die pad to V_{ss}.

1.5.13 100-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxAxx, R5F101xxAxx

D: Industrial applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxDxx, R5F101xxDxx

G: Industrial applications when $T_A = -40$ to $+105^\circ\text{C}$ products is used in the range of $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxGxx

- Cautions**
1. **The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.**
 2. **With products not provided with an $\text{EV}_{\text{DD}0}$, $\text{EV}_{\text{DD}1}$, $\text{EV}_{\text{SS}0}$, or $\text{EV}_{\text{SS}1}$ pin, replace $\text{EV}_{\text{DD}0}$ and $\text{EV}_{\text{DD}1}$ with V_{DD} , or replace $\text{EV}_{\text{SS}0}$ and $\text{EV}_{\text{SS}1}$ with V_{ss} .**
 3. **The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.**

2.3 DC Characteristics

2.3.1 Pin characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (1/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	I_{OH1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		-10.0 ^{Note 2}	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty $\leq 70\%$ ^{Note 3})	$4.0 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		-55.0	mA
			$2.7 \text{ V} \leq EV_{DD0} < 4.0 \text{ V}$		-10.0	mA
			$1.8 \text{ V} \leq EV_{DD0} < 2.7 \text{ V}$		-5.0	mA
			$1.6 \text{ V} \leq EV_{DD0} < 1.8 \text{ V}$		-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty $\leq 70\%$ ^{Note 3})	$4.0 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		-80.0	mA
			$2.7 \text{ V} \leq EV_{DD0} < 4.0 \text{ V}$		-19.0	mA
			$1.8 \text{ V} \leq EV_{DD0} < 2.7 \text{ V}$		-10.0	mA
			$1.6 \text{ V} \leq EV_{DD0} < 1.8 \text{ V}$		-5.0	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$1.6 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		-135.0 ^{Note 4}	mA
	I_{OH2}	Per pin for P20 to P27, P150 to P156	$1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$		-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$		-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0} , EV_{DD1} , V_{DD} pins to an output pin.

2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor $> 70\%$ the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and $I_{OH} = -10.0 \text{ mA}$

$$\text{Total output current of pins} = (-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA .

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{ss} = EV_{ss0} = EV_{ss1} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current <small>Note 1</small>	I_{DD1}	Operating mode HS (high-speed main) mode <small>Note 5</small>	$f_{IH} = 32 \text{ MHz}^{\text{Note 3}}$	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.6			mA
					$V_{DD} = 3.0 \text{ V}$		2.6			mA
			$f_{IH} = 24 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 5.0 \text{ V}$		6.1	9.5		mA
					$V_{DD} = 3.0 \text{ V}$		6.1	9.5		mA
		LS (low-speed main) mode <small>Note 5</small>	$f_{IH} = 16 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 5.0 \text{ V}$		3.5	5.3		mA
					$V_{DD} = 3.0 \text{ V}$		3.5	5.3		mA
		LV (low-voltage main) mode <small>Note 5</small>	$f_{IH} = 8 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 3.0 \text{ V}$		1.5	2.3		mA
					$V_{DD} = 2.0 \text{ V}$		1.5	2.3		mA
		HS (high-speed main) mode <small>Note 5</small>	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.9	6.1		mA
					Resonator connection		4.1	6.3		mA
			$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.9	6.1		mA
					Resonator connection		4.1	6.3		mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		2.5	3.7		mA
					Resonator connection		2.5	3.7		mA
		LS (low-speed main) mode <small>Note 5</small>	$f_{MX} = 8 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		1.4	2.2		mA
					Resonator connection		1.4	2.2		mA
			$f_{MX} = 8 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 2.0 \text{ V}$	Normal operation	Square wave input		1.4	2.2		mA
					Resonator connection		1.4	2.2		mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		5.4	6.5		μA
					Resonator connection		5.5	6.6		μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		5.5	6.5		μA
					Resonator connection		5.6	6.6		μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.6	9.4		μA
					Resonator connection		5.7	9.5		μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.9	12.0		μA
					Resonator connection		6.0	12.1		μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		6.6	16.3		μA
					Resonator connection		6.7	16.4		μA

(Notes and Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(TA = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate	Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 1.4 kΩ, V _b = 2.7 V	Note 1		Note 1		Note 1		bps
				2.8 Note 2		2.8 Note 2		2.8 Note 2		Mbps
				Note 3		Note 3		Note 3		bps
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 2.7 kΩ, V _b = 2.3 V	1.2 Note 4		1.2 Note 4		1.2 Note 4		Mbps
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V	Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 5.5 kΩ, V _b = 1.6 V	Notes 5, 6		Notes 5, 6		Notes 5, 6		bps
				0.43 Note 7		0.43 Note 7		0.43 Note 7		Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

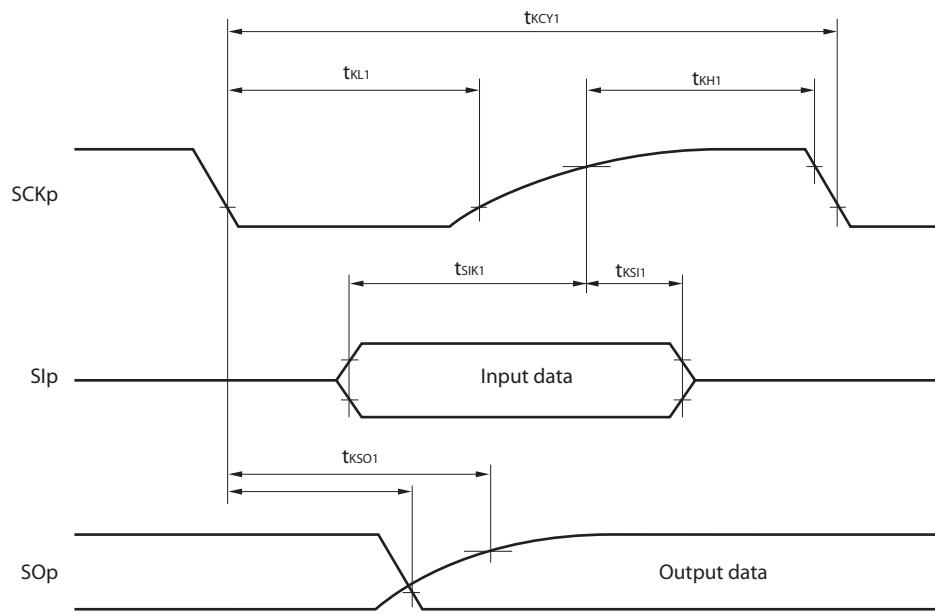
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 [\%]$$

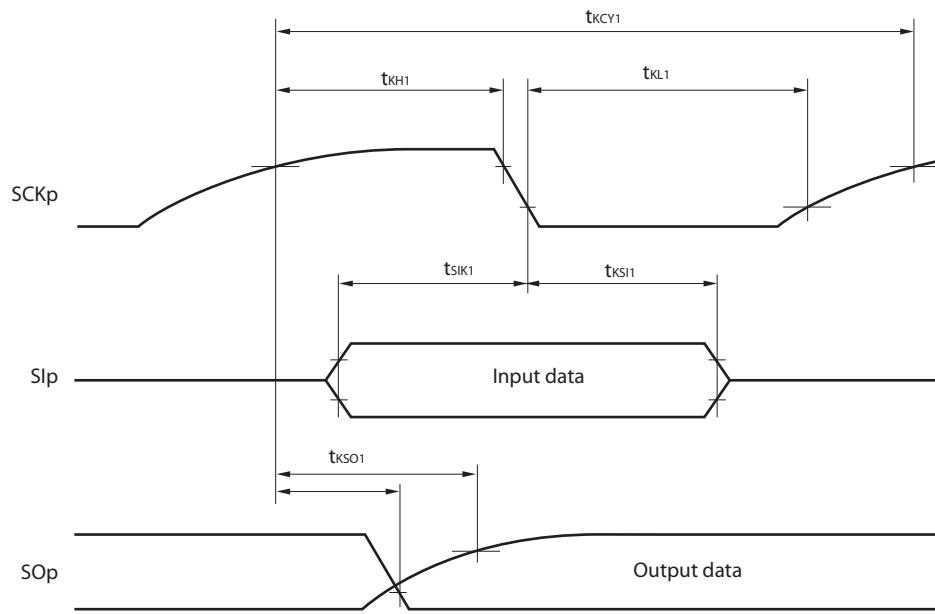
* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 2.** This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 0$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 1$.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 1$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 0$.)



- Remarks**
1. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number, n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)
 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2) $(T_A = -40$ to $+85^\circ\text{C}$, $1.8 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCL _r clock frequency	f _{SCL}	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 <small>Note 1</small>		300 <small>Note 1</small>		300 <small>Note 1</small>	kHz
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 <small>Note 1</small>		300 <small>Note 1</small>		300 <small>Note 1</small>	kHz
		4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ		400 <small>Note 1</small>		300 <small>Note 1</small>		300 <small>Note 1</small>	kHz
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		400 <small>Note 1</small>		300 <small>Note 1</small>		300 <small>Note 1</small>	kHz
		1.8 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V <small>Note 2</small> , C _b = 100 pF, R _b = 5.5 kΩ		300 <small>Note 1</small>		300 <small>Note 1</small>		300 <small>Note 1</small>	kHz
Hold time when SCL _r = "L"	t _{LOW}	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1150		1550		1550		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V <small>Note 2</small> , C _b = 100 pF, R _b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCL _r = "H"	t _{HIGH}	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	245		610		610		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	200		610		610		ns
		4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	675		610		610		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	600		610		610		ns
		1.8 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V <small>Note 2</small> , C _b = 100 pF, R _b = 5.5 kΩ	610		610		610		ns

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP}	Reference voltage (+) = V_{DD}	Reference voltage (+) = V_{BGR}
Reference voltage (-) = AV_{REFM}	Reference voltage (-) = V_{SS}	Reference voltage (-) = AV_{REFM}	Reference voltage (-) = AV_{REFM}
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI26	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		—

(1) When reference voltage (+) = AV_{REFP} /ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM} /ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq \text{AV}_{\text{REFP}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, $\text{V}_{\text{SS}} = 0 \text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $\text{AV}_{\text{REFM}} = 0 \text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$		1.2	± 3.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}		1.2	± 7.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	57		95	μs
	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
			2.7 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
			2.4 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 0.25	%FSR
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 0.50	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 0.25	%FSR
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 0.50	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 2.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 5.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 1.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 2.0	LSB
Analog input voltage	V _{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage (2.4 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, HS (high-speed main) mode)			V_{BGR} ^{Note 5}		V
		Temperature sensor output voltage (2.4 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, HS (high-speed main) mode)			V_{TMP525} ^{Note 5}		V

(Notes are listed on the next page.)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD0}		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
			TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60 to P63		0.7EV _{DD0}		6.0	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS, RESET		0.8V _{DD}		V _{DD}	V
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	V _{IL4}	P60 to P63		0		0.3EV _{DD0}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLKS, RESET		0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.
3. When high-speed on-chip oscillator and subsystem clock are stopped.
4. When high-speed system clock and subsystem clock are stopped.
5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 32 MHz
 $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 16 MHz
8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH} : High-speed on-chip oscillator clock frequency
3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	t _{KCY2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < f _{MCK}	16/f _{MCK}		ns
			f _{MCK} ≤ 20 MHz	12/f _{MCK}		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < f _{MCK}	16/f _{MCK}		ns
			f _{MCK} ≤ 16 MHz	12/f _{MCK}		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		16/f _{MCK}		ns
				12/f _{MCK} and 1000		ns
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V		t _{KCY2} /2 – 14		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V		t _{KCY2} /2 – 16		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		t _{KCY2} /2 – 36		ns
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK2}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +40		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +60		ns
Slp hold time (from SCKp↑) ^{Note 2}	t _{KSI2}	2.4 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +62		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	t _{KSO2}	C = 30 pF ^{Note 4}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/f _{MCK} +66	ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/f _{MCK} +113	ns

- Notes**
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - C is the load capacitance of the SOp output lines.
 - Transfer rate in the SNOOZE mode : MAX. 1 Mbps

Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

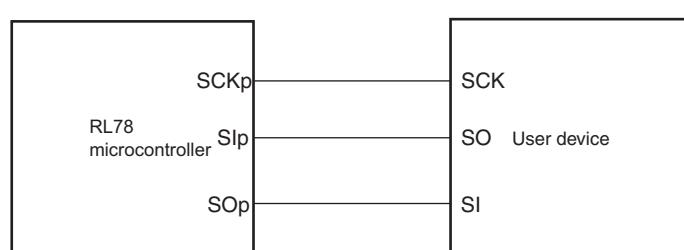
- Remarks** 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

CSI mode connection diagram (during communication at same potential)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{ss} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp↓) ^{Note}	t _{SIK1}	4.0 V ≤ EV _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	88		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	88		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	220		ns
Slp hold time (from SCKp↓) ^{Note}	t _{KSI1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	38		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	38		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SO _p output ^{Note}	t _{KSO1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		50	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		50	ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SO_p pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

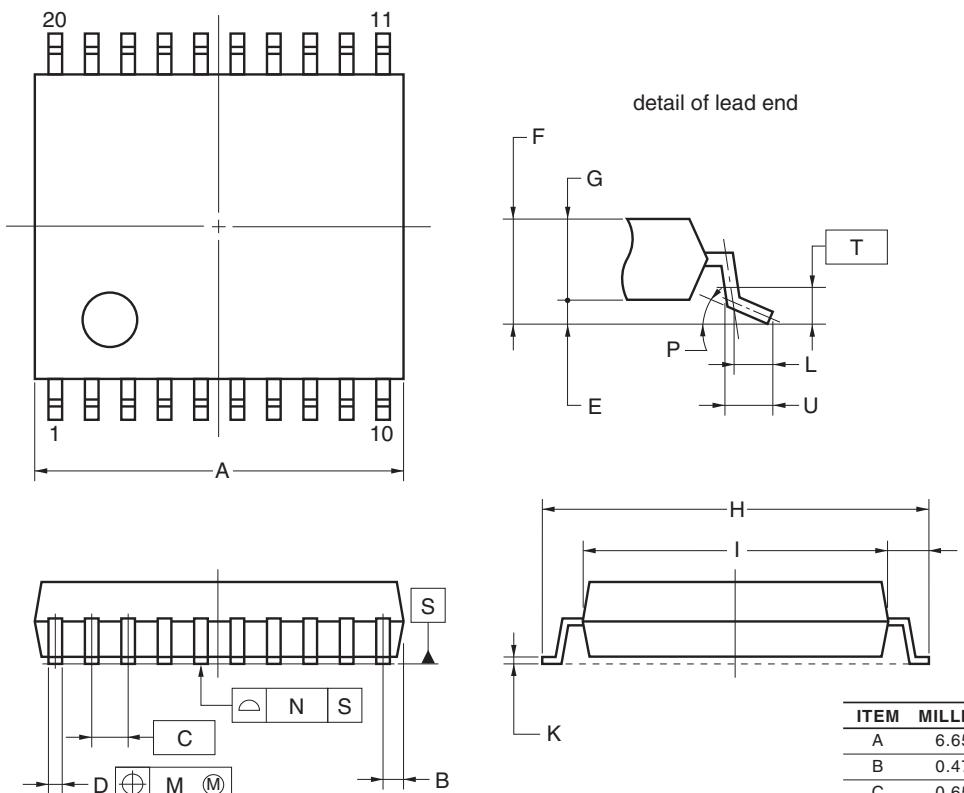
(Remarks are listed on the next page.)

4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP
 R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP
 R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP
 R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP
 R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12



NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

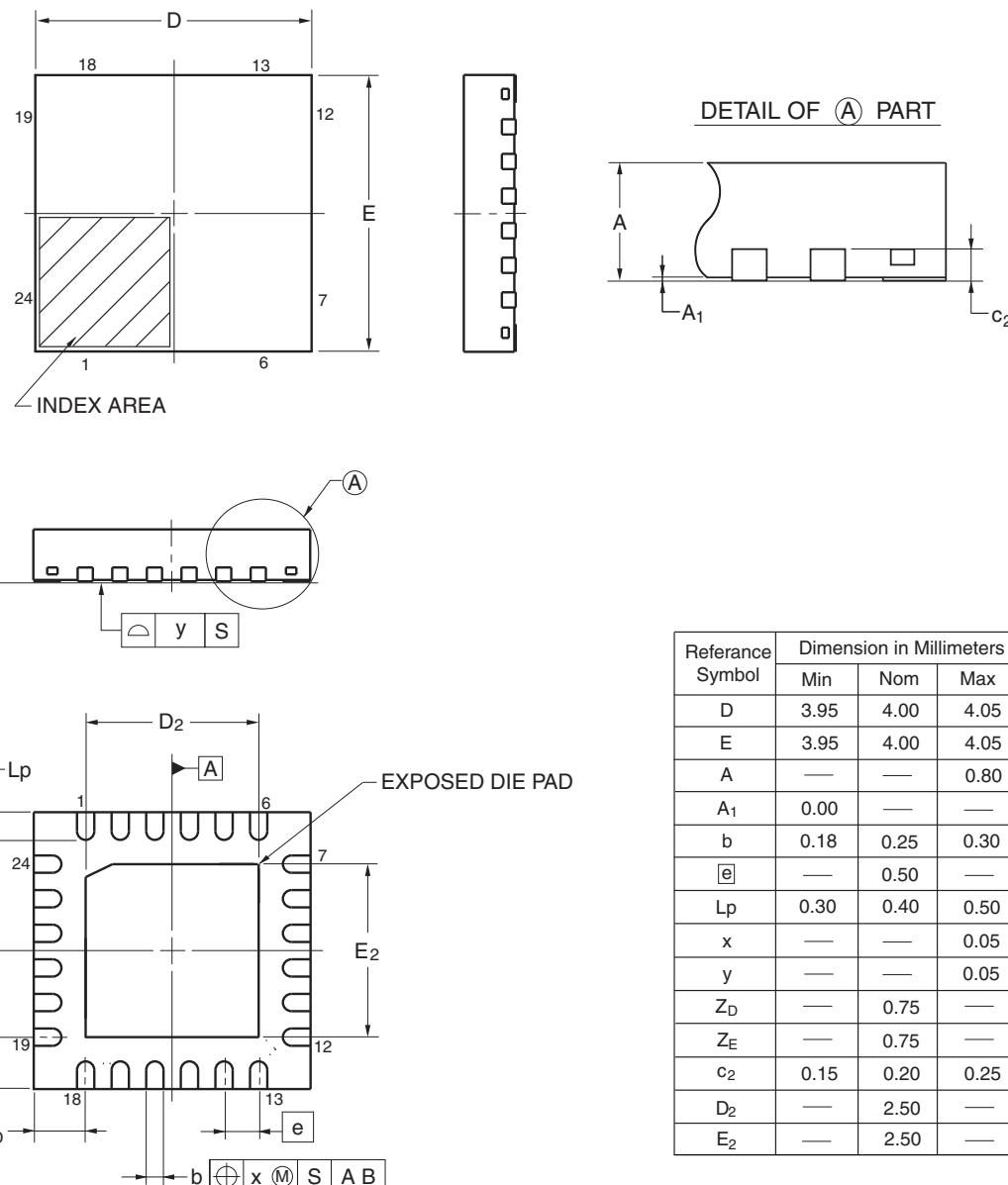
ITEM	MILLIMETERS
A	6.65±0.15
B	0.475 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

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4.2 24-pin Products

R5F1007AANA, R5F1007CANA, R5F1007DANA, R5F1007EANA
 R5F1017AANA, R5F1017CANA, R5F1017DANA, R5F1017EANA
 R5F1007ADNA, R5F1007CDNA, R5F1007DDNA, R5F1007EDNA
 R5F1017ADNA, R5F1017CDNA, R5F1017DDNA, R5F1017EDNA
 R5F1007AGNA, R5F1007CGNA, R5F1007DGNA, R5F1007EGNA

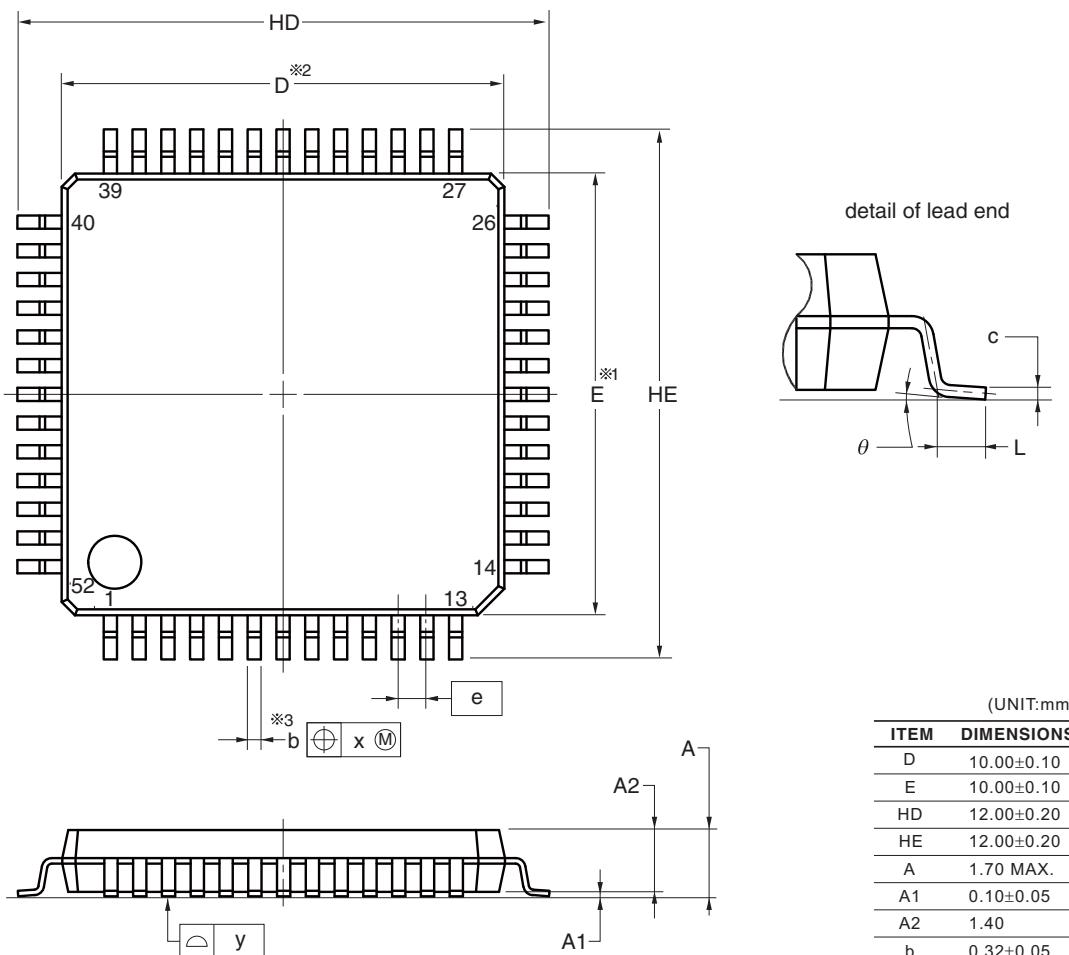
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-3	0.04



4.10 52-pin Products

R5F100JCAFA, R5F100JDAFA, R5F100JEAF, R5F100JFAFA, R5F100JGAF, R5F100JHAF, R5F100JJAF,
 R5F100JKAF, R5F100JLAF
 R5F101JCAFA, R5F101JDAFA, R5F101JEAF, R5F101JFAFA, R5F101JGAF, R5F101JHAF, R5F101JJAF,
 R5F101JKAF, R5F101JLAF
 R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JGDFA, R5F100JHDFA, R5F100JJDF,
 R5F100JKDFA, R5F100JLDFA
 R5F101JCDFA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JGDFA, R5F101JHDFA, R5F101JJDF,
 R5F101JKDFA, R5F101JLDFA
 R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



(UNIT:mm)	
ITEM	DIMENSIONS
D	10.00±0.10
E	10.00±0.10
HD	12.00±0.20
HE	12.00±0.20
A	1.70 MAX.
A1	0.10±0.05
A2	1.40
b	0.32±0.05
c	0.145±0.055
L	0.50±0.15
θ	0° to 8°
e	0.65
x	0.13
y	0.10

NOTE

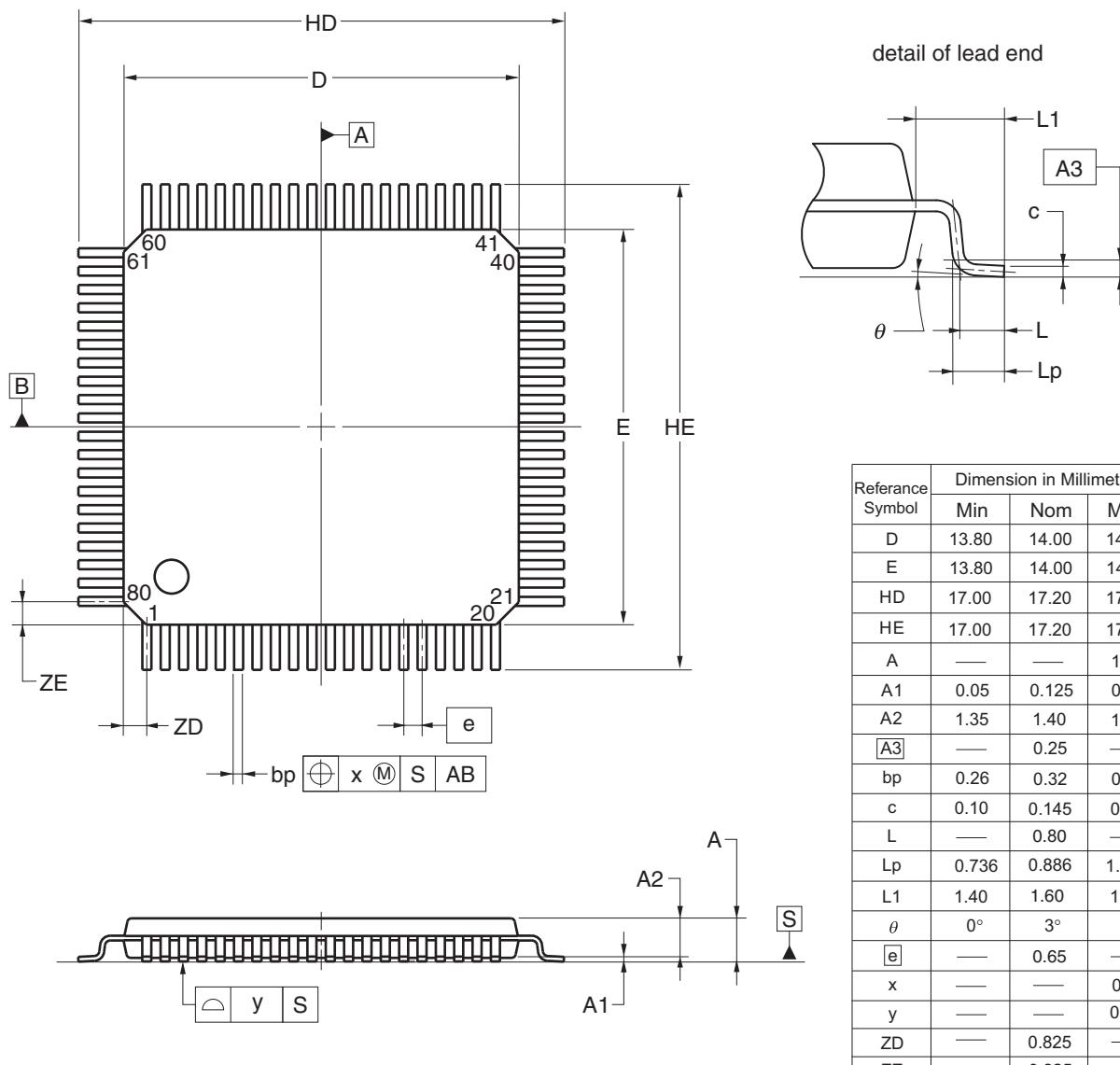
1. Dimensions “*1” and “*2” do not include mold flash.
2. Dimension “*3” does not include trim offset.

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4.12 80-pin Products

R5F100MFAFA, R5F100MGAFA, R5F100MHAFA, R5F100MJAFA, R5F100MKAFA, R5F100MLAFA
 R5F101MFAFA, R5F101MGAFA, R5F101MHAFA, R5F101MJAFA, R5F101MKAFA, R5F101MLAFA
 R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJ DFA, R5F100MK DFA, R5F100ML DFA
 R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJ DFA, R5F101MK DFA, R5F101ML DFA
 R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



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Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		109	Addition of (1) I ² C standard mode
		111	Addition of (2) I ² C fast mode
		112	Addition of (3) I ² C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)